Stealth II Rectifier 30 A, 600 V

FFH30S60S

Description

The FFH30S60S is stealth2 rectifier with soft recovery characteristics. It is silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as freewheeling of boost diode in switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Features

- High Speed Switching, $t_{rr} < 35$ ns @ $I_F = 30$ A
- High Reverse Voltage and High Reliability
- This Device is Pb-Free and is RoHS Compliant

Applications

- General Purpose
- Switching Mode Power Supply
- Boost Diode in Continuous Mode Power Factor Corrections
- Power Switching Circuits

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|--|-----------------------------------|----------------|------|
| Peak Repetitive Reverse Voltage | V_{RRM} | 600 | V |
| Working Peak Reverse Voltage | V_{RWM} | 600 | V |
| DC Blocking Voltage | V _R | 600 | V |
| Average Rectified Forward Current @ T _C = 102°C | I _{F(AV)} | 30 | Α |
| Non-Repetitive Peak Surge Current 60 Hz Single Half-Sine Wave | I _{FSM} | 300 | Α |
| Operating and Storage Temperature Range | T _J , T _{STG} | -65 to +175 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

| Parameter | Symbol | Value | Unit |
|--|-----------------|-------|------|
| Maximum Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 1.1 | °C/W |



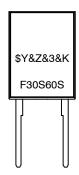
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TO-247 2 LEAD CASE 340CL

MARKING DIAGRAM



| \$Y | = ON Semiconductor Logo |
|---------|-------------------------|
| &Z | = Assembly Plant Code |
| &3 | = Numeric Date Code |
| &K | = Lot Code |
| F30S60S | = Specific Device Code |
| | |



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

PACKAGE MARKING AND ORDERING INFORMATION

| Device | Device Marking | Package | Reel Size | Tape Width | Quantity |
|-------------|----------------|-----------|-----------|------------|----------|
| FFH30S60STU | F30S60S | TO-247-2L | N/A | N/A | 50 Units |

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Unit |
|---|--|---|------------------|---------------------------|------------------|---------------|
| V _{FM} (Note 1) | I _F = 30 A I _F = 30 A | T _C = 25°C T _C = 125°C | | 2.1 1.6 | 2.6 | V |
| I _{RM} (Note 1) | V _R = 600 V V _R = 600 V | T _C = 25°C T _C = 125°C | | - - | 100 500 | μΑ |
| t _{rr} | $I_F = 1 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s, V}_R = 30 \text{ V}$ | T _C = 25°C | - | 25.2 | 30 | ns |
| t _{rr} I _{rr} S factor Q _{rr} | $I_F = 30 \text{ A}, \text{ di/dt} = 200 \text{ A/}\mu\text{s}, \text{ V}_R = 390 \text{ V}$ | T _C = 25°C | - - - | 26 2.4 0.9 43 | - - - | ns A nC |
| t _{rr} I _{rr} S factor Q _{rr} | I _F = 30 A, di/dt = 200 A/μs, V _R = 390 V | T _C = 125°C | - - - - | 75.1 6.3 0.9 238 | - - - - | ns A nC |
| W _{AVL} | Avalanche Energy (L = 40 mH) | • | 7.2 | - | - | mJ |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TEST CIRCUIT AND WAVEFORMS

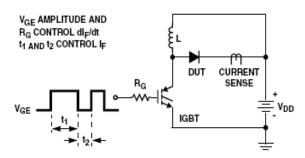


Figure 1. t_{rr} Test Circuit

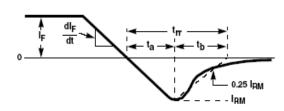


Figure 2. t_{rr} Waveforms and Definitions

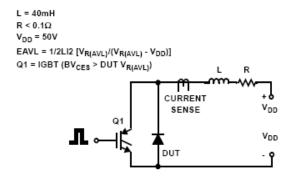


Figure 3. Avalanche Energy Test Circuit

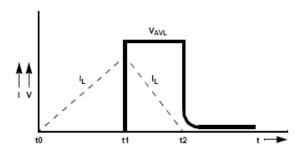


Figure 4. Avalanche Current and Voltage Definitions

^{1.} Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%

FFH30S60S

TYPICAL PERFORMANCE CHARACTERISTICS

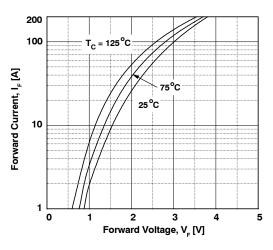


Figure 5. Typical Forward Voltage Drop vs. Forward Current

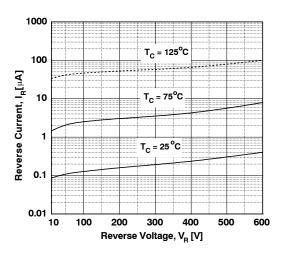


Figure 6. Typical Reverse Current vs. Reverse Voltage

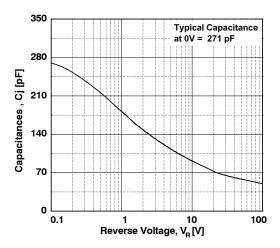


Figure 7. Typical Junction Capacitance

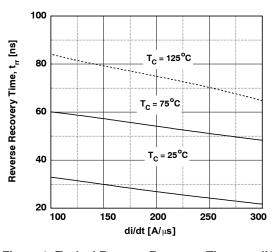


Figure 8. Typical Reverse Recovery Time vs. di/dt

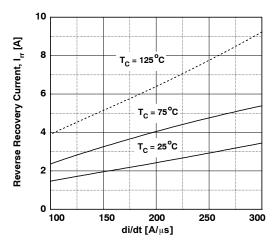


Figure 9. Typical Reverse Recovery Current vs. di/dt

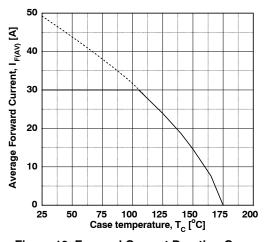
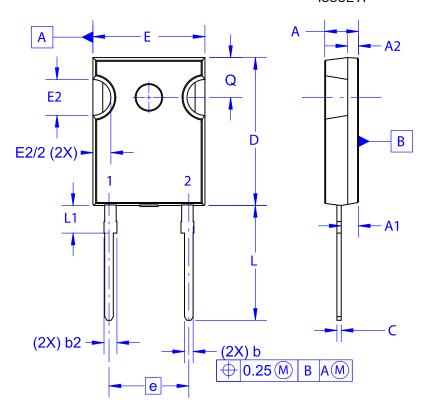


Figure 10. Forward Current Derating Curve

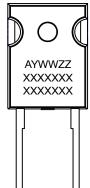
TO-247-2LD CASE 340CL **ISSUE A**





- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 2009.
 D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code

= Assembly Location

= Year

WW = Work Week

= Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

| | DATE 03 DEC 2019 | | |
|-------|------------------|---|---------|
| Ø P — | | | Ø P1 D2 |
| E1 — | | 1 | D1 |
| · | | | • |

| DIM | MILLIMETERS | | | |
|-----|-------------|-------|-------|--|
| DIM | MIN | NOM | MAX | |
| Α | 4.58 | 4.70 | 4.82 | |
| A1 | 2.29 | 2.40 | 2.66 | |
| A2 | 1.30 | 1.50 | 1.70 | |
| b | 1.17 | 1.26 | 1.35 | |
| b2 | 1.53 | 1.65 | 1.77 | |
| С | 0.51 | 0.61 | 0.71 | |
| D | 20.32 | 20.57 | 20.82 | |
| D1 | 16.37 | 16.57 | 16.77 | |
| D2 | 0.51 | 0.93 | 1.35 | |
| Е | 15.37 | 15.62 | 15.87 | |
| E1 | 12.81 | ~ | ~ | |
| E2 | 4.96 | 5.08 | 5.20 | |
| е | ~ | 11.12 | ~ | |
| L | 15.75 | 16.00 | 16.25 | |
| L1 | 3.69 | 3.81 | 3.93 | |
| ØΡ | 3.51 | 3.58 | 3.65 | |
| ØP1 | 6.61 | 6.73 | 6.85 | |
| Q | 5.34 | 5.46 | 5.58 | |
| S | 5.34 | 5.46 | 5.58 | |

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| DESCRIPTION: | TO-247-2LD | | PAGE 1 OF 1 |

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